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3.3-V RS-485 TRANSCEIVER

FEATURES

- Operates With a 3.3-V Supply
- Bus-Pin ESD Protection Exceeds 16-kV Human-Body Model (HBM)
- 1/8 Unit-Load Option Available (up to 256 Nodes on Bus)
- Optional Driver Output Transition Times for Signaling Rates ⁽¹⁾ of 1 Mbps, 10 Mbps, and 32 Mbps
- Based on ANSI TIA/EIA-485-A
- Bus-Pin Short Circuit Protection From
 -7 V to 12 V
- Open-Circuit, Idle-Bus, and Shorted-Bus Fail-Safe Receiver
- Glitch-Free Power-Up and Power-Down
 Protection for Hot-Plugging Applications
- SN75176 Footprint

APPLICATIONS

- Down-Hole Drilling
- High Temperature Environments
- Digital Motor Controls
- Utility Meters
- Chassis-to-Chassis Interconnects
- Electronic Security Stations
- Industrial Process Control
- Building Automation

bits per second (bps).

Point-of-Sale (POS) Terminals and Networks

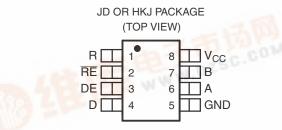
SUPPORTS EXTREME TEMPERATURE APPLICATIONS

- Controlled Baseline
- One Assembly/Test Site
- One Fabrication Site
- Available in Extreme (-55°C/210°C) Temperature Range⁽²⁾
- Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability
- Texas Instruments' high temperature products utilize highly optimized silicon (die) solutions with design and process enhancements to maximize performance over extended temperatures.

DESCRIPTION/ORDERING INFORMATION

The SN65HVD11 combines a 3-state differential line driver and differential input line receiver that operates with a single 3.3-V power supply. It is designed for balanced transmission lines and meets or exceeds ANSI TIA/EIA-485-A and ISO 8482:1993, with the exception that the thermal shutdown is removed. This differential bus transceiver is a monolithic integrated circuit designed for bidirectional data communication on multipoint bus-transmission lines. The driver and receiver have active-high and active-low enables, respectively, that can be externally connected together to function as direction control.

The driver differential outputs and receiver differential inputs connect internally to form a differential input/ output (I/O) bus port that is designed to offer minimum loading to the bus when the driver is disabled or $V_{CC} = 0$.



(2) Custom temperature ranges available



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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

(1) The signaling rate of a line is the number of voltage

transitions that are made per second expressed in the units

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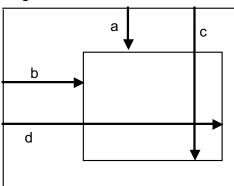
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BARE DIE INFORMATION

DIE THICKNESS	BACKSIDE FINISH	BACKSIDE POTENTIAL	BOND PAD METALLIZATION COMPOSITION
15 mils.	Silicon with backgrind	GND	Cu-Ni-Pd

Origin



Bond Pad Coordinates in Microns - Rev A

DESCRIPTION ⁽¹⁾	PAD NUMBER	а	b	С	d
R	1	69.30	372.15	185.30	489.15
~RE	2	388.75	71.50	503.75	186.50
DNC	3	722.40	55.40	839.40	172.40
DNC	4	891.40	55.40	1008.40	172.40
DE	5	1174.80	71.50	1289.80	186.50
DNC	6	1754.35	65.40	1869.35	180.40
DNC	7	1907.35	65.40	2022.35	180.40
D	8	2280.55	69.50	2395.55	184.50
DNC	9	2733.50	371.50	2848.50	486.50
GND	10	2691	1693.10	2808	1810.10
GND	11	2535	1693.10	2652	1810.10
DNC	12	2253.45	1685.65	2368.45	1800.65
А	13	1961.55	1693.10	2078.55	1810.10
В	14	799.55	1693.10	916.55	1810.10
DNC	15	498.35	1681.20	613.35	1796.20
VCC	16	244.80	1668.50	359.80	1783.50
VCC	17	91.80	1668.50	206.80	1783.50

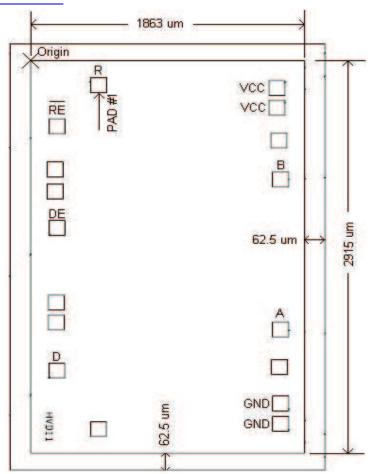
(1) DNC = Do Not Connect

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

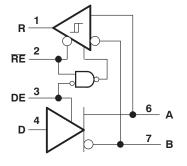
ORDERING INFORMATION⁽¹⁾

SIGNALING RATE		т	PACKAGE ⁽²⁾			
SIGNALING RATE	UNIT LOADS	CDIP		'A CDIP		TOP-SIDE MARKING
10 Mbps	1/8	–55°C to 210°C	SN65HVD11SJD	SN65HVD11SJD		
10 Mbps	1/8	–55°C to 210°C	SN65HVD11SKGDA			
10 Mbps	1/8	–55°C to 210°C	SN65HVD11SHKJ	SN65HVD11SHKJ		

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

(2) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS⁽¹⁾⁽²⁾

over operating free-air temperature range (unless otherwise noted)

				VALUE	UNIT
V_{C}	Supply voltage range			-0.3 to 6	V
С					
	Voltage range at A or B		–9 to 14	V	
	Input voltage range at D, D	DE, R, or RE	–0.5 to V _{CC} + 0.5	V	
	Voltage input range, transi	ent pulse, A and B, through 100	-50 to 50	V	
Ιo	Receiver output current rar	nge		-11 to 11	mA
		Human-Body Model	A, B, and GND	16	
	Electrostatic discharge	(HBM) ⁽³⁾	All pins	4	kV
		Charged-Device Model (CDM) ⁽⁴⁾	All pins charge	1	
	Continuous total power dis	sipation	See Dissipation Ratings Table		

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.

(4) Tested in accordance with JEDEC Standard 22, Test Method C101.

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RECOMMENDED OPERATING CONDITIONS

			T _A = -	55°C to	125°C	T _A = 210°C			
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		3		3.6	3		3.6	V
V_{I} or V_{IC}	Voltage at any bus terminal (separately or co	ommon mode)	-7 ⁽¹⁾		12	-7 ⁽¹⁾		12	V
V _{IH}	High-level input voltage	D, DE, RE	2		V _{CC}	2		V _{CC}	V
V _{IL}	Low-level input voltage	D, DE, RE	0		0.8	0		0.8	V
V _{ID}	Differential input voltage	Figure 8	-12		12	-12		12	V
	High-level output current	Driver	-60			-60			0
I _{OH}		Receiver	-8			-8			mA
		Driver			60			60	
I _{OL}	Low-level output current	Receiver			8			8	mA
RL	Differential load resistance		54	60		54	60		Ω
CL	Differential load capacitance			50			50		pF
	Signaling rate				10			10	Mbps
T _J ⁽²⁾	Operating junction temperature			129			214		°C

The algebraic convention, in which the least-positive (most-negative) limit is designated as minimum, is used in this data sheet.
 See Thermal Characteristics table for information regarding this specification.

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INSTRUMENTS

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DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	DADAMETER		TECT	CONDITIONS	T _A = -5	55°C to 1	25°C	TA	= 210°C ⁽	1)	UNIT
	PARAMETER	(TEST	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V _{IK}	Input clamp	voltage	I _I = -18 mA		-1.5			-1.5			V
			I _O = 0		2		V _{CC}	2		V _{CC}	
V _{OD}	V _{OD} Differential output voltage		$R_L = 54 \Omega$, See Figure 2		1.0			1			V
			$V_{\text{test}} = -7 \text{ V to } 1$	2 V, See Figure 3	1.0			1			
Δ V _{OD}	Change in m of differential voltage		$V_{\text{test}} = -7 \text{ V to 1}$ Figure 3	2 V,See Figure 2 and	-0.2		0.2	-0.25		0.25	V
V _{OC(PP)}	Peak-to-peak		See Figure 4			400			400		mV
V _{OC(SS)}	Steady-state common-mo voltage		See Figure 4		1.4		2.5	1.4		2.5	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage		See Figure 4		-0.06		0.06	-0.06		0.06	V
I _{OZ}	High-impeda current	nce output	See receiver in	ee receiver input currents							
	Input	D			-100		0	-100		3	۸
l	current	DE			0		100	0		100	μA
I _{OS}	Short-circuit current	output	$-7 \text{ V} \leq \text{V}_{O} \leq 12$	V	-250		250	-250		250	mA
C _(OD)	Differential o capacitance	utput	V _{OD} = 0.4 sin (4 DE = 0 V	4E6πt) + 0.5 V,		18			18		pF
			$\label{eq:RE} \begin{array}{l} \overline{RE} = V_{CC}, \\ D \text{ and } DE = \\ V_{CC}, \\ No \text{ load} \end{array}$	Receiver disabled and driver enabled		11	15.5		14	18	mA
I _{CC}	Supply current		$\label{eq:rescaled} \begin{split} \overline{RE} &= V_{CC},\\ D &= V_{CC},\\ DE &= 0 \;V,\\ No \;load \end{split}$	Receiver disabled and driver disabled (standby)		2.5	20		175	450	μA
			$\overline{\text{RE}} = 0 \text{ V},$ D and DE = V _{CC} , No load	Receiver enabled and driver enabled		11	15.5		11	18	mA

(1) Minimum and maximum parameters are characterized for operation at $T_A = 210^{\circ}$ C but may not be production tested at that temperature. Production test limits with statistical guardbands are used to ensure high temperature performance.

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DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A = -{	T _A = -55°C to 125°C			T _A = 210°C ⁽¹⁾		
		TEST CONDITIONS	MIN	MIN TYP MAX		MIN TYP MAX		MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		18	25	40	18	25	40	ns
t _{PHL}	Propagation delay time, high-to-low-level output		18	25	40	18	25	40	ns
t _r	Differential output signal rise time	$R_L = 54 \Omega, C_L = 50 pF,$ See Figure 5	10	21	30	10	22	30	ns
t _f	Differential output signal fall time		10	21	30	10	22	30	ns
t _{sk(p)}	Pulse skew (t _{PHL} – t _{PLH})				2.5			2.5	ns
t _{sk(pp)} ⁽²⁾	Part-to-part skew (t _{PHL} or t _{PLH})	-			11			11	ns
t _{PZH}	Propagation delay time, high-impedance to high-level output	$R_L = 110 \Omega, \overline{RE} = 0 V,$ See Figure 6			55			55	ns
t _{PHZ}	Propagation delay time, high-level to high-impedance output				55			55	ns
t _{PZL}	Propagation delay time, high-impedance to low-level output	$R_L = 110 \Omega, \overline{RE} = 0 V,$ See Figure 7			55			55	ns
t _{PLZ}	Propagation delay time, low-level to high-impedance output				75			75	ns
t _{PZH}	Propagation delay time, standby to high-level output	$R_L = 110 \Omega, \overline{RE} = 3 V,$ See Figure 6			6			6	μs
t _{PZL}	Propagation delay time, standby to low-level output	$R_L = 110 \Omega, \overline{RE} = 3 V,$ See Figure 7			6			6	μs

(1) Minimum and maximum parameters are characterized for operation at $T_A = 210^{\circ}C$ but may not be production tested at that temperature. Production test limits with statistical guardbands are used to ensure high temperature performance.

(2) t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

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RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

		терт	CONDITIONS		T _A =	55°C to	125°C	TA	= 210°C	(1)	UNIT
	PARAMETER	IESI	CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V _{IT+}	Positive-going input threshold voltage	I _O = -8 mA					-0.0 1			-0.0 1	V
V _{IT-}	Negative-going input threshold voltage	I _O = 8 mA			-0.2			-0.2			V
V _{hys}	Hysteresis voltage (V _{IT+} –V _{IT–})					35			41		mV
V _{IK}	Enable-input clamp voltage	I _I = -18 mA			-1.5			-1.5			V
V _{он}	High-level output voltage	V_{ID} = 200 mV, I_{OH}	= –8 mA, See	Figure 8	2.4			2.4			V
V _{OL}	Low-level output voltage	$V_{ID} = -200 \text{ mV}, I_{OL} = 8 \text{ mA}, \text{See Figure 8}$					0.4			0.4	V
oz	High-impedance state output current	$V_{O} = 0 \text{ or } V_{CC,} \text{ RE}$	= V _{CC}		-1		1	-1		1	μΑ
		V_A or V_B = 12 V				0.075	0.11		0.1	0.15	
I.	Bus input current	V_A or V_B = 12 V, V_{CC} = 0 V		Other input		0.085	0.13		0.12	0.16	mA
'I	Bus input current	V_A or $V_B = -7 V$		at 0 V	-0.1	-0.05		-0.3	-0.15		IIIA
		V_A or $V_B = -7 V$, V	_{CC} = 0 V		-0.1	-0.05		-0.3	-0.15		
Ін	High-level input current, RE	V _{IH} = 2 V			-30		0	-30		3	μA
IIL	Low-level input current, RE	V _{IL} = 0.8 V			-30		0	-30		0	μA
CID	Differential input capacitance	V _{ID} = 0.4 sin (4E6)	τt) + 0.5 V, DE	at 0 V		15			18		pF
		$\overline{RE} = 0 V,$ D and DE = 0 V, No load	Receiver enab			5	8		7.5	10	mA
I _{CC}	Supply current	$\overline{RE} = V_{CC},$ $D = V_{CC},$ DE = 0 V, No load	Receiver disa driver disable			2.5	20		175	450	μΑ
		$\overline{\text{RE}} = 0 \text{ V},$ D and DE = V _{CC} , No load	Receiver enabled			11	15.5		14	18	mA

(1) Minimum and maximum parameters are characterized for operation at $T_A = 210^{\circ}C$ but may not be production tested at that temperature. Production test limits with statistical guardbands are used to ensure high temperature performance.

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RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	DADAMETED	TEST CONDITIONS	T _A =	55°C to 1	25°C	Тд	= 210°C	(1)	UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		30	55	70	30	55	70	ns
t _{PHL}	Propagation delay time, high-to-low-level output	$V_{ID} = -1.5 V \text{ to } 1.5 V,$ $C_L = 15 \text{ pF},$	30	55	70	30	55	70	ns
t _{sk(p)}	Pulse skew (t _{PHL} – t _{PLH})	See Figure 9			4			4	ns
t _{sk(pp)} ⁽²⁾	Part-to-part skew				15			15	ns
t _r	Output signal rise time	$C_{l} = 15 \text{pF},$	1	3	5	1	4	5	ns
t _f	Output signal fall time	See Figure 9	1	3	5	1	4	5	ns
t _{PZH} ⁽¹⁾	Output enable time to high level				15			15	ns
t _{PZL} ⁽¹⁾	Output enable time to low level	C _L = 15 pF, DE = 3 V,			15			15	ns
t _{PHZ}	Output disable time from high level	See Figure 10			20			20	ns
t _{PLZ}	Output disable time from low level				15			15	ns
t _{PZH} ⁽²⁾	Propagation delay time, standby-to-high-level output	C _L = 15 pF, DE = 0,			6			6	μs
t _{PZL} ⁽²⁾	Propagation delay time, standby-to-low-level output	See Figure 11			6			6	μs

(1) Minimum and maximum parameters are characterized for operation at $T_A = 210^{\circ}$ C but may not be production tested at that temperature. Production test limits with statistical guardbands are used to ensure high temperature performance.

(2) t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

THERMAL CHARACTERISTICS FOR JD PACKAGE

over operating free-air temperature range unless otherwise noted (1)

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
0	Junction-to-ambient thermal	High-K board ⁽³⁾ , No airflow	JD pkg		64.9		°C/W
θ_{JA}	resistance ⁽²⁾	No airflow	JD pkg		83.4		C/W
θ_{JB}	Junction-to-board thermal resistance	High-K board without underfill	JD pkg		27.9		°C/W
θ_{JC}	Junction-to-case thermal resistance		JD pkg		6.49		°C/W
P _D	Device power dissipation	$\begin{array}{l} R_L = 60 \ \Omega, \ C_L = 50 \ pF, \\ DE = V_{CC}, \ RE = 0 \ V, \\ Input \ to \ D \ a \ 50\% \ duty \ cycle \ square \\ wave \ at \ indicated \ signaling \ rate \end{array}$	HVD11 (10 Mbps)		165		mW

(1) See Application Information section for an explanation of these parameters.

(2) The intent of θ_{JA} specification is solely for a thermal performance comparison of one package to another in a standardized environment. This methodology is not meant to and will not predict the performance of a package in an application-specific environment.

(3) JED51-7, High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages

THERMAL CHARACTERISTICS FOR HKJ PACKAGE

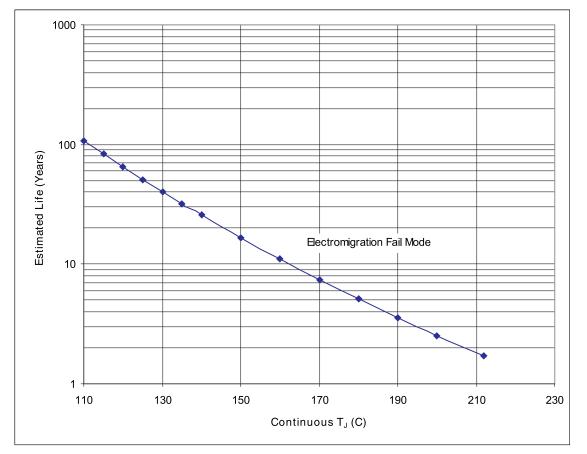
over operating free-air temperature range (unless otherwise noted)

	PARAMETERS	MAX	UNIT
θ_{JC}	Junction-to-case thermal resistance (to bottom of case)	5.7	°C/W
θ_{JC}	Junction-to-case thermal resistance (to top of case lid - as if formed dead bug)	13.7	°C/W

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- A. See data sheet for absolute maximum and minimum recommended operating conditions.
- B. Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).

Figure 1. SN65HVD11SJD / SN65HVD11SKGDA / SN65HVD11SHKJ Operating Life Derating Chart

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PARAMETER MEASUREMENT INFORMATION

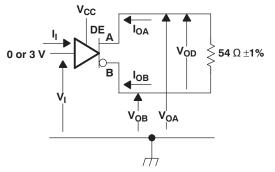
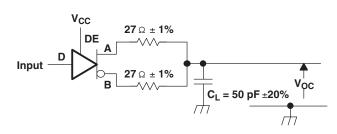


Figure 2. Driver V_{OD} Test Circuit and Voltage and Current Definitions



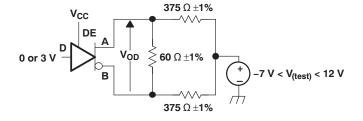
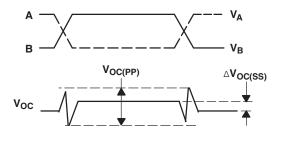


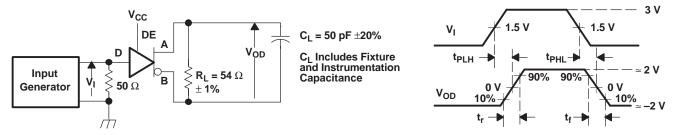
Figure 3. Driver V_{OD} With Common-Mode Loading Test Circuit



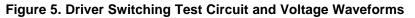
A. Input: PRR = 500 kHz, 50% Duty Cycle, t_r <6ns, t_f <6ns, Z_O = 50 Ω

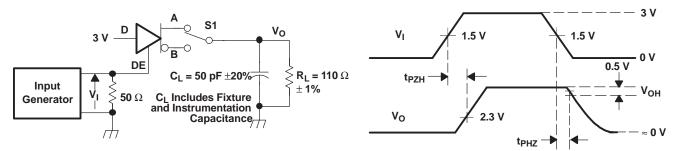
B. CL Includes fixture and instrumentation capacitance

Figure 4. Test Circuit and Definitions for Driver Common-Mode Output Voltage



Generator: PRR = 500 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω





Generator: PRR = 500 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω

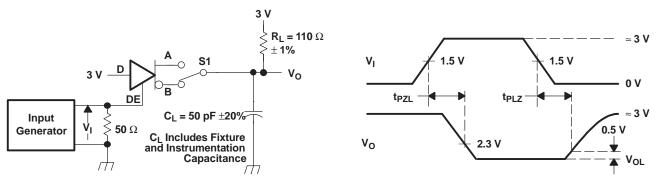
Figure 6. Driver High-Level Enable and Disable Time Test Circuit and Voltage Waveforms

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Generator: PRR = 500 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω

Figure 7. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

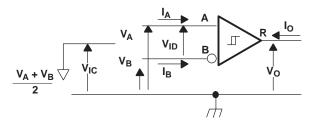
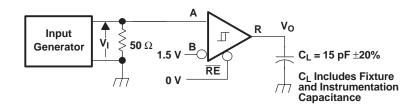
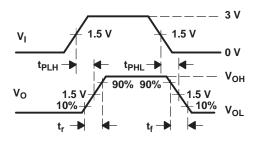


Figure 8. Receiver Voltage and Current Definitions



Generator: PRR = 500 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω



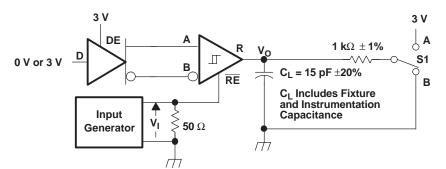




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PARAMETER MEASUREMENT INFORMATION (continued)



Generator: PRR = 500 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω

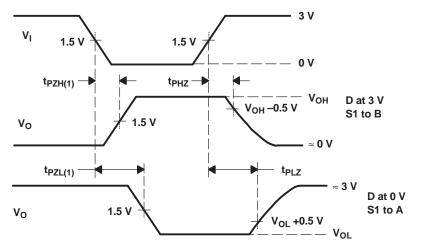
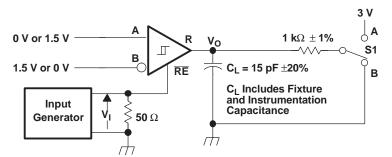


Figure 10. Receiver Enable and Disable Time Test Circuit and Voltage Waveforms With Drivers Enabled

TEXAS INSTRUMENTS

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PARAMETER MEASUREMENT INFORMATION (continued)



Generator: PRR = 100 kHz, 50% Duty Cycle, t_r <6 ns, t_f <6 ns, Z_o = 50 Ω

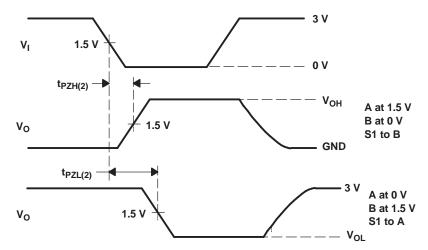
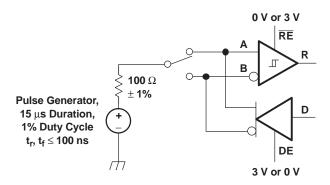


Figure 11. Receiver Enable Time From Standby (Driver Disabled)



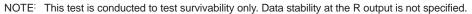


Figure 12. Test Circuit, Transient Over Voltage Test



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PARAMETER MEASUREMENT INFORMATION (continued)

FUNCTION TABLES

DRIVER⁽¹⁾

		OUTPUTS					
INPUT D	ENABLE DE	Α	В				
Н	Н	Н	L				
L	Н	L	Н				
Х	L	Z	Z				
Open	Н	Н	L				

(1) H = high level
 L = low level
 Z = high impedance
 X = irrelevant

? = indeterminate

RECEIVER⁽¹⁾

DIFFERENTIAL INPUTS $V_{ID} = V_A - V_B$	ENABLE RE	OUTPUT R
$V_{ID} \leq -0.2 V$	L	L
$-0.2 \text{ V} < \text{V}_{\text{ID}} < -0.01 \text{ V}$	L	?
−0.01 V ≤ V _{ID}	L	Н
Х	Н	Z
Open circuit	L	Н
Short circuit	L	Н

(1) H = high levelL = low level

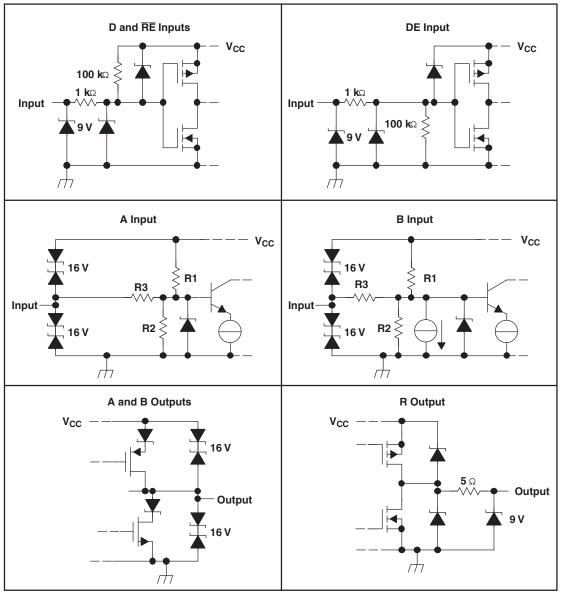
Z = high impedanceX = irrelevant

? = indeterminate



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EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

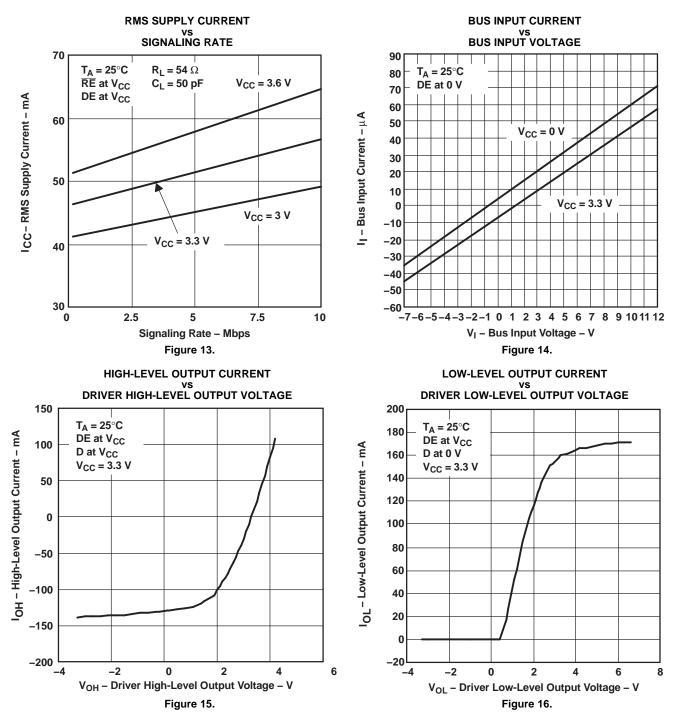
R1/R2 = 36 kΩ R3 = 180 kΩ

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TYPICAL CHARACTERISTICS

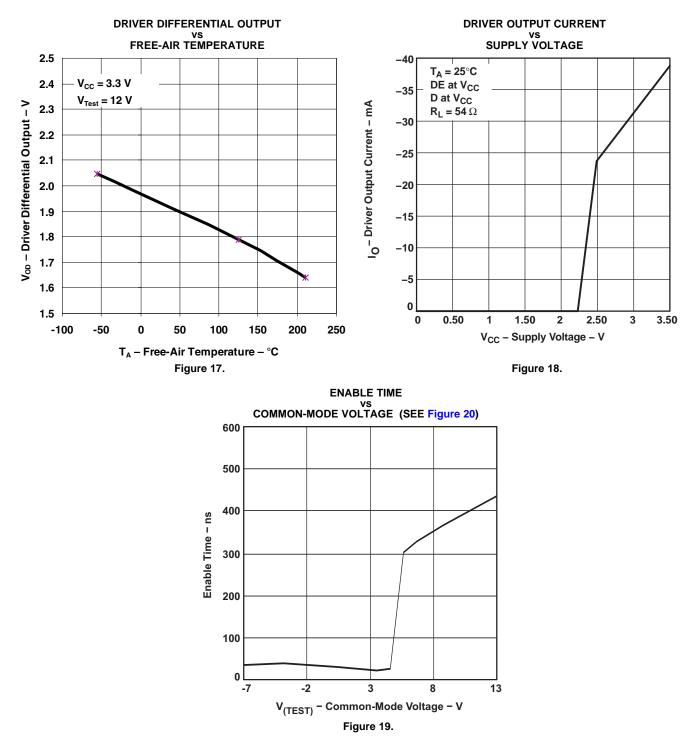




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TYPICAL CHARACTERISTICS (continued)

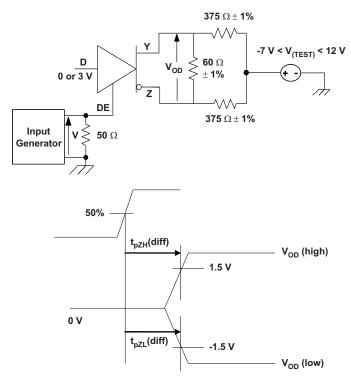


Figure 20. Driver Enable Time From DE to V_{OD}

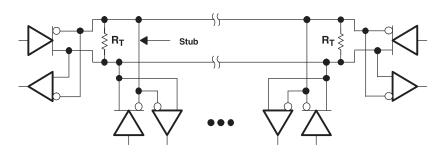
The time $t_{pZL}(x)$ is the measure from DE to $V_{OD}(x)$. V_{OD} is valid when it is greater than 1.5 V.



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APPLICATION INFORMATION



256 Devices on Bus

NOTE: The line should be terminated at both ends with its characteristic impedance ($R_T = Z_O$). Stub lengths off the main line should be kept as short as possible.

Figure 21. Typical Application Circuit

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THERMAL CHARACTERISTICS OF IC PACKAGES

 θ_{JA} (Junction-to-Ambient Thermal Resistance) is defined as the difference in junction temperature to ambient temperature divided by the operating power.

 θ_{JA} is *not* a constant and is a strong function of:

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

 θ_{JA} can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures. θ_{JA} is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-k board gives *average* in-use condition thermal performance, and it consists of a single copper trace layer 25 mm long and 2-oz thick. The high-k board gives best *case* in-use condition, and it consists of two 1-oz buried power planes with a single copper trace layer 25 mm long and 2-oz thick. A 4% to 50% difference in θ_{JA} can be measured between these two test cards.

 θ_{JC} (Junction-to-Case Thermal Resistance) is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

 θ_{JC} is a useful thermal characteristic when a heatsink is applied to package. It is *not* a useful characteristic to predict junction temperature because it provides pessimistic numbers if the case temperature is measured in a nonstandard system and junction temperatures are backed out. It can be used with θ_{JB} in 1-dimensional thermal simulation of a package system.

 θ_{JB} (Junction-to-Board Thermal Resistance) is defined as the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold-plate structure. θ_{JB} is only defined for the high-k test card.

 θ_{JB} provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system, see Figure 22.

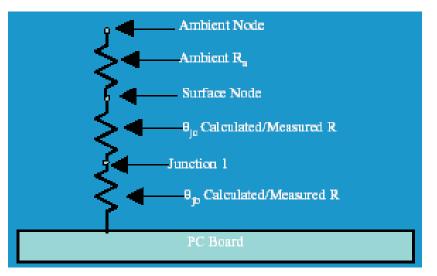


Figure 22. Thermal Resistance

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PACKAGING INFORMATION

_									
	Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Pe
	SN65HVD11SHKJ	ACTIVE	CFP	HKJ	8	1	TBD	Call TI	N / A for Pkg
	SN65HVD11SJD	ACTIVE	CDIP SB	JDJ	8	1	TBD	POST-PLATE	N / A for Pkg
	SN65HVD11SKGDA	ACTIVE	XCEPT	KGD	0	130	TBD	Call TI	N / A for Pkg

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new **PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www. information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retard in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF SN65HVD11-HT :

• Catalog: SN65HVD11



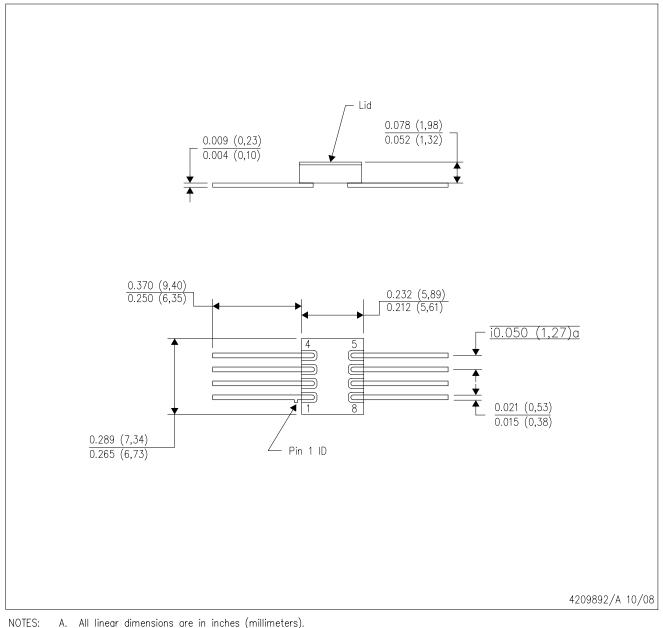
PACKAG

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

HKJ (R-CDFP-F8)

CERAMIC DUAL FLATPACK

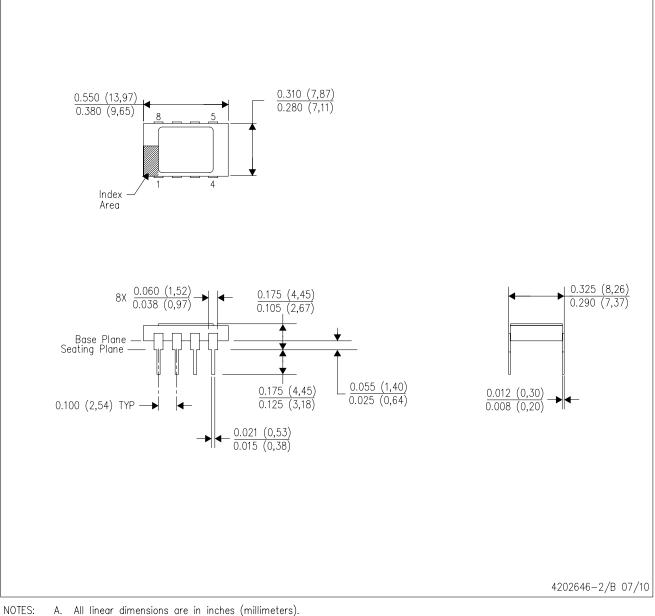


- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- c. This brokage can be hermetically sealed with a metal lid.
- D. The terminals will be gold plated.



JDJ (R-CDIP-T8)

CERAMIC DUAL IN-LINE PACKAGE

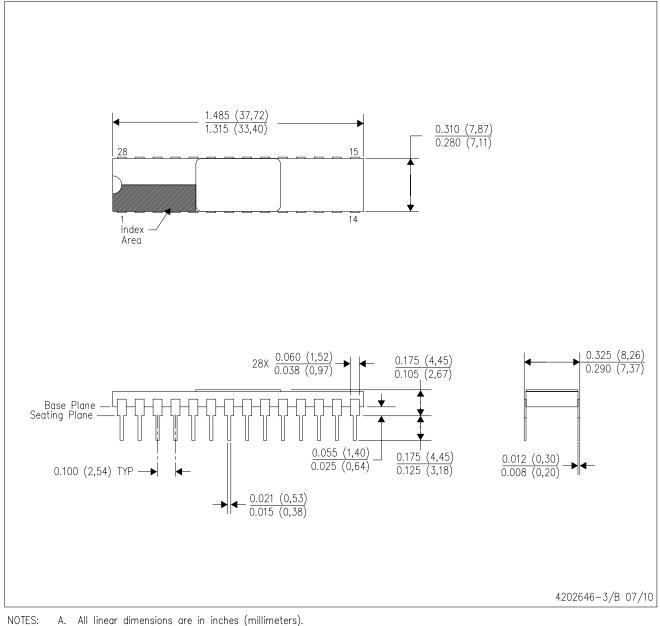


- B. This drawing is subject to change without notice.
- C. Ceramic quad flatpack with flat leads brazed to non-conductive tie bar carrier.
- D. This package is hermetically sealed with a metal lid.
- E. The leads are gold plated and can be solderdipped.
- F. Leads not shown for clarity purposes.
- G. Lid and heat sink are connected to GND leads.



JDJ (R-CDIP-T28)

CERAMIC DUAL IN-LINE PACKAGE



- B. This drawing is subject to change without notice.
- C. Ceramic quad flatpack with flat leads brazed to non-conductive tie bar carrier.
- D. This package is hermetically sealed with a metal lid.
- E. The leads are gold plated and can be solderdipped.
- F. Leads not shown for clarity purposes.
- G. Lid and heat sink are connected to GND leads.



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